# **BPW77NA, BPW77NB**

## Vishay Semiconductors



## Silicon NPN Phototransistor, RoHS Compliant



### FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): Ø 4.7
- · High photo sensitivity
- High radiant sensitivity
- · Suitable for visible and near infrared radiation
- · Fast response times
- Angle of half sensitivity:  $\varphi = \pm 10^{\circ}$
- · Base terminal connected
- Hermetically sealed package
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

### **APPLICATIONS**

· Detector in electronic control and drive circuits

## DESCRIPTION

BPW77 is a silicon NPN phototransistor with high radiant sensitivity in hermetically sealed TO-18 package with base terminal and glass lens. It is sensitive to visible and near infrared radiation.

PRODUCT SUMMARY					
COMPONENT	I <sub>ca</sub> (mA)	φ <b>(deg)</b>	λ <sub>0.1</sub> (nm)		
BPW77NA	7.5 to 15	± 10	450 to 1080		
BPW77NB	> 10	± 10	450 to 1080		

#### Note

Test condition see table "Basic Characteristics"

### **ORDERING INFORMATION**

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
BPW77NA	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
BPW77NB	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
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#### Note

MOQ: minimum order quantity

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector base voltage		V <sub>CBO</sub>	80	V
Collector emitter voltage		V <sub>CEO</sub>	70	V
Emitter base voltage		V <sub>EBO</sub>	5	V
Collector current		Ι <sub>C</sub>	50	mA
Collector peak current	$t_p/T$ = 0.5, $t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA
Total power dissipation	T <sub>amb</sub> ≤ 25 °C	Pv	250	mW
Junction temperature		Tj	125	°C
Operating temperature range		T <sub>amb</sub>	- 40 to + 125	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 125	°C
Soldering temperature	t ≤ 5 s	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	R <sub>thJA</sub>	400	K/W
Thermal resistance junction/gase		R <sub>thJC</sub>	150	K/W

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified



COMPLIANT



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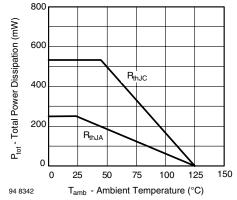


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Collector emitter breakdown voltage	I <sub>C</sub> = 1 mA	V <sub>(BR)CEO</sub>	70			V		
Collector emitter dark current	V <sub>CE</sub> = 20 V, E = 0	I <sub>CEO</sub>		1	100	nA		
Collector emitter capacitance	V <sub>CE</sub> = 5 V, f = 1 MHz, E = 0	C <sub>CEO</sub>		6		pF		
Angle of half sensitivity		φ		± 10		deg		
Wavelength of peak sensitivity		λρ		850		nm		
Range of spectral bandwidth		λ <sub>0.1</sub>		450 to 1080		nm		
Collector emitter saturation voltage	$\begin{array}{l} E_{e} = 1 \ mW/cm^2,  \lambda = 950 \ nm, \\ I_{C} = 1 \ mA \end{array}$	V <sub>CEsat</sub>		0.15	0.3	V		
Turn-on time	$V_{S}$ = 5 V, $I_{C}$ = 5 mA, $R_{L}$ = 100 $\Omega$	t <sub>on</sub>		6		μs		
Turn-off time	$V_{S}$ = 5 V, $I_{C}$ = 5 mA, $R_{L}$ = 100 $\Omega$	t <sub>off</sub>		5		μs		
Cut-off frequency	$V_{S}$ = 5 V, $I_{C}$ = 5 mA, $R_{L}$ = 100 $\Omega$	f <sub>c</sub>		110		kHz		

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light ourrent	$E_e = 1 \text{ mW/cm}^2$ , $\lambda = 950 \text{ nm}$ ,	BPW77NA	I <sub>ca</sub>	<sub>ca</sub> 7.5 15	mA		
Collector light current	$V_{CE} = 5 V$	BPW77NB	I <sub>ca</sub>	10		45	mA

### **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

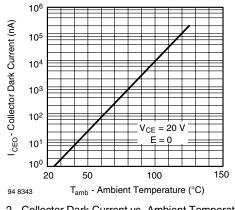


Fig. 2 - Collector Dark Current vs. Ambient Temperature

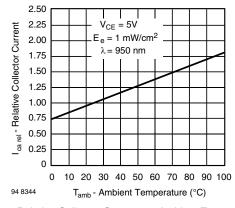


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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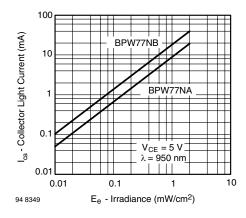


Fig. 4 - Collector Light Current vs. Irradiance

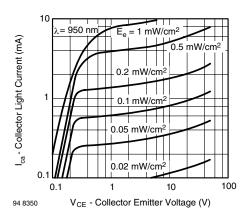


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

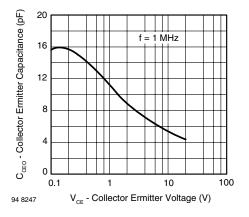


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

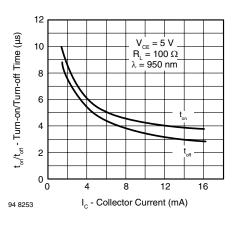


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

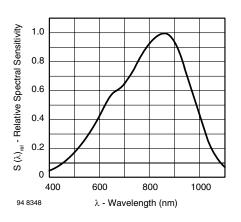


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

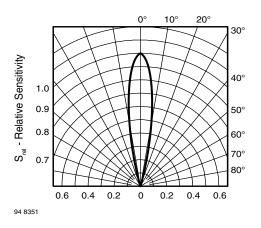


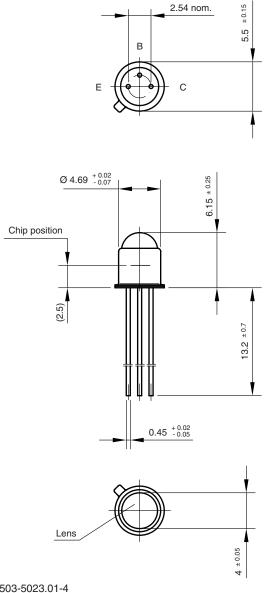
Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

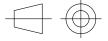


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### **PACKAGE DIMENSIONS** in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.503-5023.01-4 Issue:1; 01.07.96 96 12180



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